

## Silicon PNP Power Transistors

## TIP42/42A/42B/42C

**DESCRIPTION**

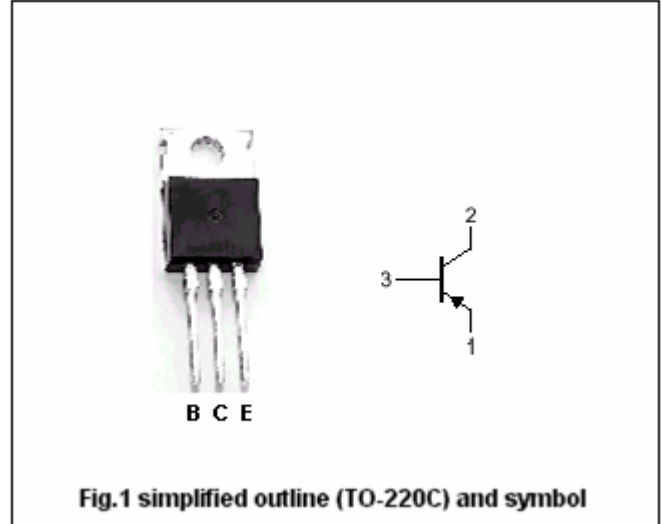
- With TO-220C package
- Complement to type TIP41/41A/41B/41C

**APPLICATIONS**

- For medium power linear switching applications

**PINNING**

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

**ABSOLUTE MAXIMUM RATINGS(T<sub>c</sub>=25 °C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	TIP42	-40	V
		TIP42A	-60	
		TIP42B	-80	
		TIP42C	-100	
V <sub>CEO</sub>	Collector-emitter voltage	TIP42	-40	V
		TIP42A	-60	
		TIP42B	-80	
		TIP42C	-100	
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-5	V
I <sub>C</sub>	Collector current (DC)		-6	A
I <sub>CM</sub>	Collector current-Pulse		-10	A
I <sub>B</sub>	Base current		-2	A
P <sub>C</sub>	Collector power dissipation	T <sub>c</sub> =25 °C	65	W
		T <sub>a</sub> =25 °C	2	
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-65~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	TIP42	I <sub>C</sub> =30mA; I <sub>B</sub> =0	-40			V
		TIP42A		-60			
		TIP42B		-80			
		TIP42C		-100			
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage		I <sub>C</sub> =-6A; I <sub>B</sub> =-0.6A			-1.5	V
V <sub>BE</sub>	Base-emitter on voltage		I <sub>C</sub> =-6A; V <sub>CE</sub> =-4V			-2.0	V
I <sub>CES</sub>	Collector cut-off current	TIP42	V <sub>CE</sub> =-40V; V <sub>EB</sub> =0			-0.4	mA
		TIP42A	V <sub>CE</sub> =-60V; V <sub>EB</sub> =0				
		TIP42B	V <sub>CE</sub> =-80V; V <sub>EB</sub> =0				
		TIP42C	V <sub>CE</sub> =-100V; V <sub>EB</sub> =0				
I <sub>CEO</sub>	Collector cut-off current	TIP41/41A	V <sub>CE</sub> =-30V; I <sub>B</sub> =0			-0.7	mA
		TIP41B/41C	V <sub>CE</sub> =-60V; I <sub>B</sub> =0				
I <sub>EBO</sub>	Emitter cut-off current		V <sub>EB</sub> =-5V; I <sub>C</sub> =0			-1.0	mA
h <sub>FE-1</sub>	DC current gain		I <sub>C</sub> =-0.3A; V <sub>CE</sub> =-4V	30			
h <sub>FE-2</sub>	DC current gain		I <sub>C</sub> =-3A; V <sub>CE</sub> =-4V	15		75	
f <sub>T</sub>	Transition frequency		I <sub>C</sub> =-0.5A; V <sub>CE</sub> =-10V	3			MHz

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PACKAGE OUTLINE

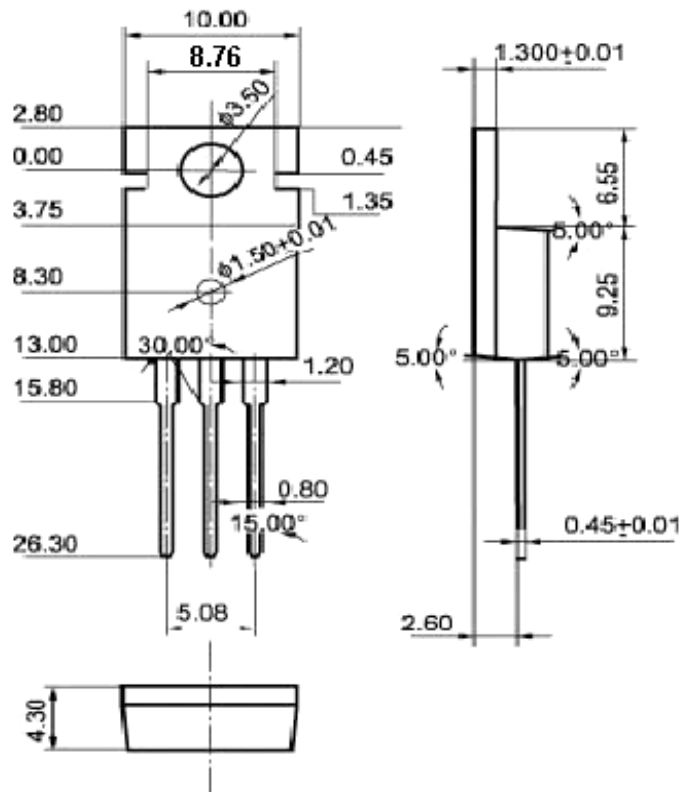


Fig.2 Outline dimensions

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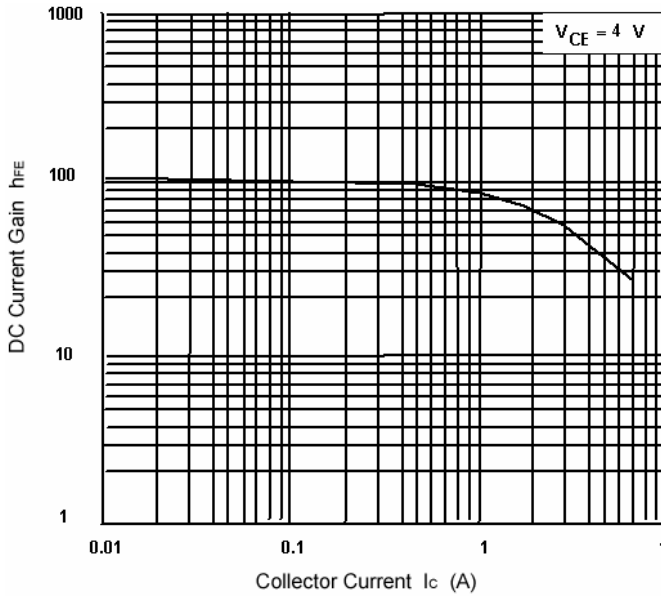


Fig.3 DC current Gain

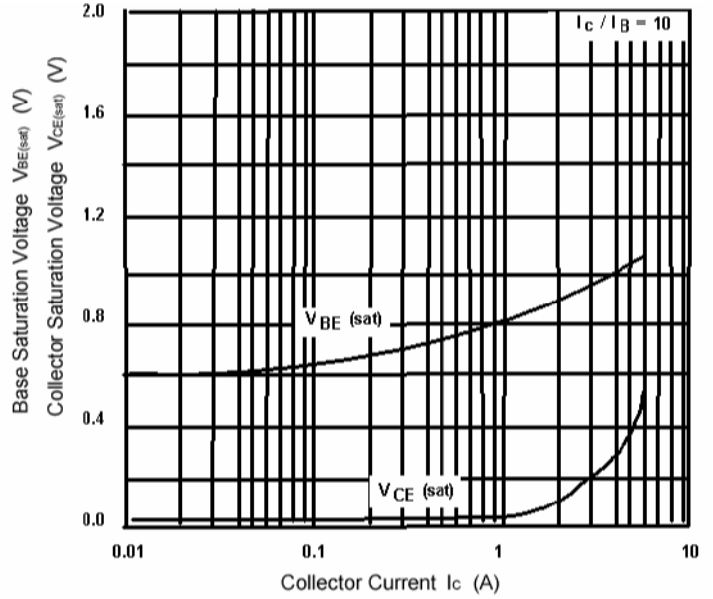


Fig.4 Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage

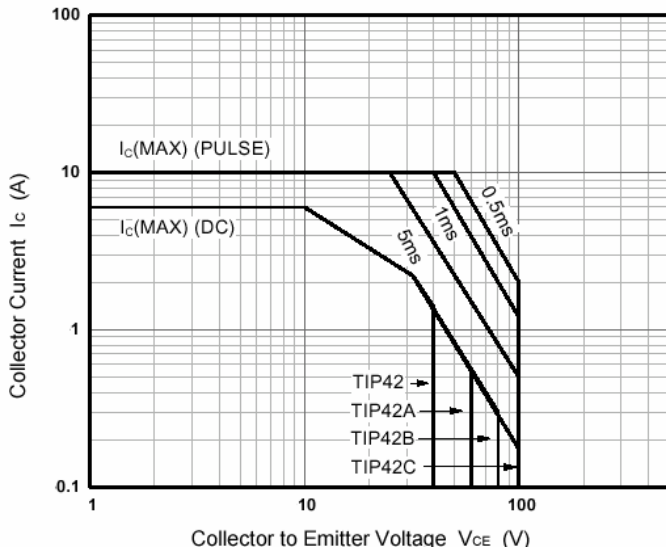


Fig.5 Safe Operating Area